

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS IV)

TPC8113

Lithium Ion Battery Applications
 Notebook PC Applications
 Portable Equipment Applications

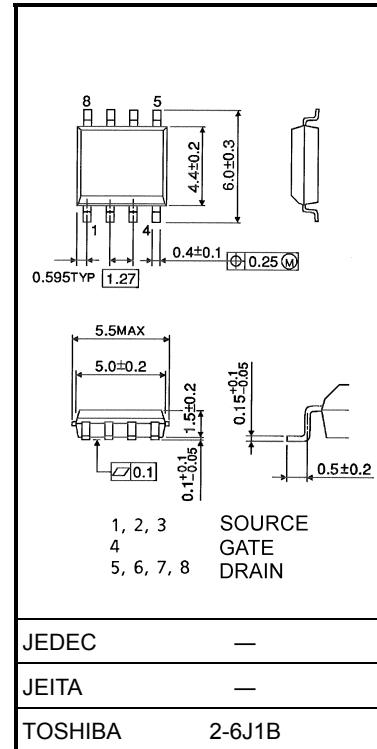
- Small footprint due to small and thin package
- Low drain-source ON resistance: $R_{DS(ON)} = 8\text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 23\text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = -10\text{ }\mu\text{A}$ (max) ($V_{DS} = -30\text{ V}$)
- Enhancement mode: $V_{th} = -0.8\text{ to }-2.0\text{ V}$ ($V_{DS} = -10\text{ V}$, $I_D = -1\text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	-30	V
Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)	V_{DGR}	-30	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	-11
	Pulse (Note 1)	I_{DP}	-44
Drain power dissipation ($t = 10\text{ s}$)	(Note 2a)	P_D	1.9
	(Note 2b)	P_D	1.0
Single pulse avalanche energy (Note 3)	E_{AS}	31.5	mJ
Avalanche current	I_{AR}	-11	A
Repetitive avalanche energy (Note 2a) (Note 4)	E_{AR}	0.19	mJ
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$

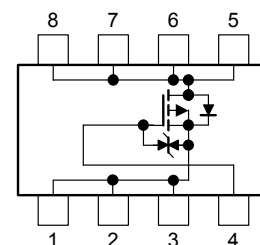
Note 1, Note 2, Note 3 and Note 4: See the next page.
 This transistor is an electrostatic-sensitive device. Please handle with caution.

Unit: mm



Weight: 0.080 g (typ.)

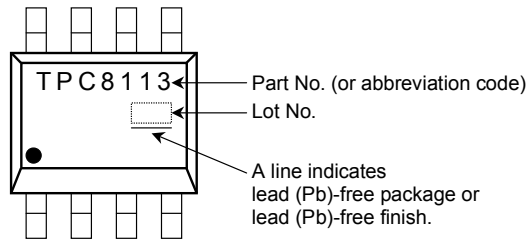
Circuit Configuration



Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th(ch-a)}$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th(ch-a)}$	125	°C/W

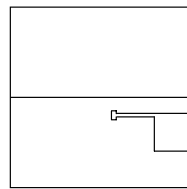
Marking (Note 5)



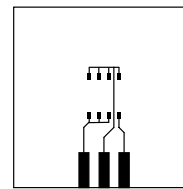
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:

(a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



(a)



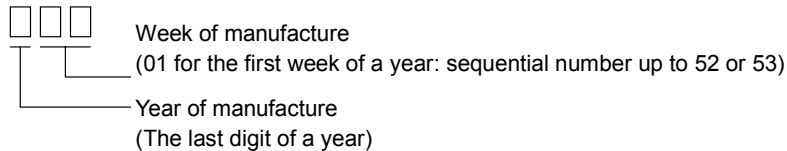
(b)

Note 3: $V_{DD} = -24\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 0.2\text{ mH}$, $R_G = 25\ \Omega$, $I_{AR} = -11\text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1.

※ Weekly code: (Three digits)



Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-OFF current		I_{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-10	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	—	—	V
		$V_{(BR)DSX}$	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	-15	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	—	-2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = -4 \text{ V}, I_D = -5.5 \text{ A}$	—	12	18	$\text{m}\Omega$
			$V_{GS} = -10 \text{ V}, I_D = -5.5 \text{ A}$	—	8	10	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -5.5 \text{ A}$	11	23	—	S
Input capacitance		C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	4500	—	pF
Reverse transfer capacitance		C_{rSS}		—	540	—	
Output capacitance		C_{oss}		—	650	—	
Switching time	Rise time	t_r	<p>$V_{GS} = 0 \text{ V}$ $V_{GS} = -10 \text{ V}$ $I_D = -5.5 \text{ A}$ V_{OUT} 4.7Ω $R_L = 2.7 \Omega$ $V_{DD} \approx -15 \text{ V}$ Duty $\leq 1\%$, $t_w = 10 \mu\text{s}$</p>	—	6	—	ns
	Turn-ON time	t_{on}		—	13	—	
	Fall time	t_f		—	120	—	
	Turn-OFF time	t_{off}		—	340	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx -24 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -11 \text{ A}$	—	107	—	nC
Gate-source charge 1		Q_{gs1}		—	12	—	
Gate-drain ("miller") charge		Q_{gd}		—	20	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	-44	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = -11 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.2	V

